# Fei Zhuge

List of Publications by Year
in descending order

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|---|---|---|---|
| 78<br>papers | 3,822<br>citations | 101384<br>36<br>h-index | 123241<br>61<br>g-index |
| 79<br>all docs | 79<br>docs citations | 79<br>times ranked | 4421<br>citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Nonvolatile resistive switching in graphene oxide thin films. Applied Physics Letters, 2009, 95, . | 1.5 | 228 |
| 2 | p-type conduction in Nâ€“Al co-doped ZnO thin films. Applied Physics Letters, 2004, 85, 3134-3135. | 1.5 | 219 |
| 3 | Ultrasensitive Memristive Synapses Based on Lightly Oxidized Sulfide Films. Advanced Materials, 2017, 29, 1606927. | 11.1 | 158 |
| 4 | Mechanism of nonvolatile resistive switching in graphene oxide thin films. Carbon, 2011, 49, 3796-3802. | 5.4 | 141 |
| 5 | Resistance switching in polycrystalline BiFeO3 thin films. Applied Physics Letters, 2010, 97, . | 1.5 | 139 |
| 6 | Effect of top electrodes on photovoltaic properties of polycrystalline BiFeO<sub>3</sub>based thin film capacitors. Nanotechnology, 2011, 22, 195201. | 1.3 | 136 |
| 7 | Nonvolatile resistive switching memory based on amorphous carbon. Applied Physics Letters, 2010, 96, . | 1.5 | 133 |
| 8 | Allâ€Optically Controlled Memristor for Optoelectronic Neuromorphic Computing. Advanced Functional Materials, 2021, 31, 2005582. | 7.8 | 123 |
| 9 | Structural, Chemical, Optical, and Electrical Evolution of SnO<sub>x</sub> Films Deposited by Reactive rf Magnetron Sputtering. ACS Applied Materials & Interfaces, 2012, 4, 5673-5677. | 4.0 | 118 |
| 10 | Mechanism for resistive switching in an oxide-based electrochemical metallization memory. Applied Physics Letters, 2012, 100, . | 1.5 | 117 |
| 11 | High-temperature tolerance in WTi-Al 2 O 3 cermet-based solar selective absorbing coatings with low thermal emissivity. Nano Energy, 2017, 37, 232-241. | 8.2 | 108 |
| 12 | Improvement of resistive switching in Cu/ZnO/Pt sandwiches by weakening the randomicity of the formation/rupture of Cu filaments. Nanotechnology, 2011, 22, 275204. | 1.3 | 106 |
| 13 | Nonvolatile resistive switching in metal/La-doped BiFeO<sub>3</sub>/Pt sandwiches. Nanotechnology, 2010, 21, 425202. | 1.3 | 104 |
| 14 | Optoelectronic neuromorphic thin-film transistors capable of selective attention and with ultra-low power dissipation. Nano Energy, 2019, 62, 772-780. | 8.2 | 103 |
| 15 | Strain and its effect on optical properties of Al-N codoped ZnO films. Journal of Applied Physics, 2006, 99, 023503. | 1.1 | 91 |
| 16 | Ambipolar inverters using SnO thin-film transistors with balanced electron and hole mobilities. Applied Physics Letters, 2012, 100, . | 1.5 | 90 |
| 17 | ZnO p-n homojunctions and ohmic contacts to Alâ€“N-co-doped p-type ZnO. Applied Physics Letters, 2005, 87, 092103. | 1.5 | 88 |
| 18 | Improvement of reproducible resistance switching in polycrystalline tungsten oxide films by in situ oxygen annealing. Applied Physics Letters, 2010, 96, . | 1.5 | 80 |

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|---|---|---|---|
| 19 | ZnO light-emitting diodes fabricated on Si substrates with homobuffer layers. Applied Physics Letters, 2007, 91, . | 1.5 | 74 |
| 20 | Memristive Synapses for Brainâ€Inspired Computing. Advanced Materials Technologies, 2019, 4, 1800544. | 3.0 | 72 |
| 21 | Synaptic devices based on purely electronic memristors. Applied Physics Letters, 2016, 108, . | 1.5 | 71 |
| 22 | Nonvolatile bistable resistive switching in a new polyimide bearing 9-phenyl-9H-carbazole pendant. Journal of Materials Chemistry, 2012, 22, 520-526. | 6.7 | 70 |
| 23 | Semiconducting ZnSnN2 thin films for Si/ZnSnN2 p-n junctions. Applied Physics Letters, 2016, 108, . | 1.5 | 59 |
| 24 | Electrical characterization of ZnO-based homojunctions. Applied Physics Letters, 2006, 89, 053501. | 1.5 | 56 |
| 25 | Mechanism for resistive switching in chalcogenide-based electrochemical metallization memory cells. AIP Advances, 2015, 5, . | 0.6 | 56 |
| 26 | Microstructure dependence of leakage and resistive switching behaviours in Ce-doped BiFeO<sub>3</sub> thin films. Journal Physics D: Applied Physics, 2011, 44, 415104. | 1.3 | 53 |
| 27 | Electrochromism of Nanocrystal-in-Glass Tungsten Oxide Thin Films under Various Conduction Cations. Inorganic Chemistry, 2019, 58, 2089-2098. | 1.9 | 53 |
| 28 | Photonic Synapses for Ultrahighâ€Speed Neuromorphic Computing. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900082. | 1.2 | 53 |
| 29 | Determination of some basic physical parameters of SnO based on SnO/Si pn heterojunctions. Applied Physics Letters, 2015, 106, . | 1.5 | 52 |
| 30 | Roles of silver oxide in the bipolar resistance switching devices with silver electrode. Applied Physics Letters, 2011, 98, . | 1.5 | 46 |
| 31 | Band Offset Engineering in ZnSnN<sub>2</sub>-Based Heterojunction for Low-Cost Solar Cells. ACS Photonics, 2018, 5, 2094-2099. | 3.2 | 46 |
| 32 | Electrically controlled electron transfer and resistance switching in reduced graphene oxide noncovalently functionalized with thionine. Journal of Materials Chemistry, 2012, 22, 16422. | 6.7 | 42 |
| 33 | Templateâ€Free Growth of Wellâ€Ordered Silver Nano Forest/Ceramic Metamaterial Films with Tunable Optical Responses. Advanced Materials, 2017, 29, 1605324. | 11.1 | 42 |
| 34 | Formation of quasi-aligned ZnCdO nanorods and nanoneedles. Journal of Crystal Growth, 2005, 283, 373-377. | 0.7 | 39 |
| 35 | Rapid synthesis and photoluminescence of novel ZnO nanotetrapods. Journal of Crystal Growth, 2005, 274, 447-452. | 0.7 | 38 |
| 36 | Thin Film Solar Cell Based on ZnSnN<sub>2</sub>/SnO Heterojunction. Physica Status Solidi - Rapid Research Letters, 2018, 12, 1700332. | 1.2 | 38 |

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|---|---|---|---|
| 37 | Substrate Biasing Effect on the Physical Properties of Reactive RF-Magnetron-Sputtered Aluminum Oxide Dielectric Films on ITO Glasses. ACS Applied Materials & Interfaces, 2014, 6, 2255-2261. | 4.0 | 31 |
| 38 | Silver Nanoparticles with an Armor Layer Embedded in the Alumina Matrix To Form Nanocermet Thin Films with Sound Thermal Stability. ACS Applied Materials & Interfaces, 2014, 6, 11550-11557. | 4.0 | 29 |
| 39 | Plasmonic AgAl Bimetallic Alloy Nanoparticle/Al<sub>2</sub>O<sub>3</sub> Nanocermet Thin Films with Robust Thermal Stability for Solar Thermal Applications. Advanced Materials Interfaces, 2016, 3, 1600248. | 1.9 | 29 |
| 40 | Nanocomposite Wâ€“4.5%ThO2 thermionic cathode. Materials Letters, 2003, 57, 2776-2779. | 1.3 | 26 |
| 41 | p-type ZnO films by codoping of nitrogen and aluminum and ZnO-based pâ€“n homojunctions. Journal of Crystal Growth, 2005, 283, 413-417. | 0.7 | 26 |
| 42 | Flexible Electrochromic V<sub>2</sub>O<sub>5</sub>Thin Films with Ultrahigh Coloration Efficiency on Graphene Electrodes. Journal of the Electrochemical Society, 2018, 165, D183-D189. | 1.3 | 25 |
| 43 | Improved Nâ€“Al codoped p-type ZnO thin films by introduction of a homo-buffer layer. Journal of Crystal Growth, 2005, 274, 425-429. | 0.7 | 21 |
| 44 | Dependence of properties of Nâ€“Al codoped p-type ZnO thin films on growth temperature. Applied Surface Science, 2005, 245, 109-113. | 3.1 | 21 |
| 45 | Anomalous rectification in a purely electronic memristor. Applied Physics Letters, 2016, 109, 143505. | 1.5 | 21 |
| 46 | Effects of growth ambient on electrical properties of Alâ€“N co-doped p-type ZnO films. Thin Solid Films, 2005, 476, 272-275. | 0.8 | 20 |
| 47 | Memristors based on amorphous ZnSnO films. Materials Letters, 2019, 249, 169-172. | 1.3 | 20 |
| 48 | Forming-free resistive switching in a nanoporous nitrogen-doped carbon thin film with ready-made metal nanofilaments. Carbon, 2014, 76, 459-463. | 5.4 | 19 |
| 49 | Single-crystalline metal filament-based resistive switching in a nitrogen-doped carbon film containing conical nanopores. Applied Physics Letters, 2015, 106, 083104. | 1.5 | 19 |
| 50 | Control of ZnO nanowire growth and optical properties in a vapor deposition process. Journal of Materials Science and Technology, 2017, 33, 850-855. | 5.6 | 19 |
| 51 | Broadband Optoelectronic Synaptic Thinâ€Film Transistors Based on Oxide Semiconductors. Physica Status Solidi - Rapid Research Letters, 2020, 14, 1900630. | 1.2 | 19 |
| 52 | The electrical properties of n-ZnO/p-SnO heterojunction diodes. Applied Physics Letters, 2016, 109, 123507. | 1.5 | 17 |
| 53 | Effect of post-annealing on structural and electrochromic properties of Mo-doped V2O5 thin films. Journal of Sol-Gel Science and Technology, 2016, 77, 604-609. | 1.1 | 17 |
| 54 | Ultralow operation voltages of a transparent memristor based on bilayer ITO. Applied Physics Letters, 2020, 116, 221602. | 1.5 | 17 |

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|---|---|---|---|
| 55 | Al concentration dependence of electrical and photoluminescent properties of co-doped ZnO films. Chemical Physics Letters, 2007, 437, 203-206. | 1.2 | 16 |
| 56 | Alâ€“N codoping and p-type conductivity in ZnO using different nitrogen sources. Surface and Coatings Technology, 2005, 198, 354-356. | 2.2 | 15 |
| 57 | Defect-related vibrational and photoluminescence spectroscopy of a codoped ZnOâ€‰:â€‰Alâ€‰:â€‰N film. Journal Physics D: Applied Physics, 2006, 39, 2339-2342. | 1.3 | 15 |
| 58 | Reproducibility and stability of Nâ€“Al codoped p-type ZnO thin films. Journal of Materials Science, 2006, 41, 467-470. | 1.7 | 15 |
| 59 | Retinaâ€Inspired Twoâ€Terminal Optoelectronic Neuromorphic Devices with Lightâ€Tunable Shortâ€Term Plasticity for Selfâ€Adjusting Sensing. Advanced Intelligent Systems, 2022, 4, . | 3.3 | 15 |
| 60 | Carrier localization in codoped ZnO:N:Al films. Solid State Communications, 2006, 138, 542-545. | 0.9 | 14 |
| 61 | Hybrid oxide brain-inspired neuromorphic devices for hardware implementation of artificial intelligence. Science and Technology of Advanced Materials, 2021, 22, 326-344. | 2.8 | 14 |
| 62 | Combined control of the cation and anion to make ZnSnON thin films for visible-light phototransistors with high responsivity. Journal of Materials Chemistry C, 2017, 5, 6480-6487. | 2.7 | 12 |
| 63 | Emerging Artificial Neuron Devices for Probabilistic Computing. Frontiers in Neuroscience, 2021, 15, 717947. | 1.4 | 9 |
| 64 | Coexistence of two types of metal filaments in oxide memristors. AIP Advances, 2017, 7, . | 0.6 | 8 |
| 65 | Structural and Electrochromic Properties of Undoped and Mo-Doped V<sub>2</sub>O<sub>5</sub> Thin Films by a Two-Electrode Electrodeposition. Journal of Nanoscience and Nanotechnology, 2018, 18, 7502-7507. | 0.9 | 7 |
| 66 | Broadband hyperbolic metamaterial covering the whole visible-light region. Optics Letters, 2019, 44, 2970. | 1.7 | 7 |
| 67 | Preparation and photoluminescent investigation of h-BN-like layered material B4CN4. Journal of Crystal Growth, 2008, 310, 3869-3872. | 0.7 | 6 |
| 68 | Ternary compound B4CN4 prepared by direct nitridation of B4C. Journal of Alloys and Compounds, 2008, 466, 299-303. | 2.8 | 6 |
| 69 | Proton conducting sodium-alginate-gated oxide thin-film transistors with varying device structure. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 3103-3109. | 0.8 | 6 |
| 70 | Specific phase modulation and infrared photon confinement in solar selective absorbers. Applied Materials Today, 2020, 18, 100533. | 2.3 | 6 |
| 71 | Aqueous solution-processed, self-flattening AlOx:Y dielectrics for fully-transparent thin-film transistors. Ceramics International, 2019, 45, 15883-15891. | 2.3 | 5 |
| 72 | Low-Temperature Synthesis of Microâ€“Mesoporous TiO2â€“SiO2 Composite Film Containing Feâ€“N Co-Doped Anatase Nanocrystals for Photocatalytic NO Removal. Catalysis Letters, 2021, 151, 2396-2407. | 1.4 | 4 |

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|---|---|---|---|
| 73 | Advances in Resistive Switching Memories Based on Graphene Oxide. , 0, , . | | 3 |
| 74 | Optoelectronic Neuromorphic Computing: Allâ€Optically Controlled Memristor for Optoelectronic Neuromorphic Computing (Adv. Funct. Mater. 4/2021). Advanced Functional Materials, 2021, 31, 2170027. | 7.8 | 1 |
| 75 | Bipolar resistance switching in multiferroic BiFeO3 polycrystalline films. , 2010, , . | | 0 |
| 76 | Non-Volatile Resistive Switching in Graphene Oxide Thin Films. , 0, , . | | 0 |
| 77 | The same batch enabled threshold voltage tuning for verticallyâ€or laterallyâ€gated transparent InZnO thinâ€film transistors. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600918. | 0.8 | 0 |
| 78 | Ultrasensitive Memristive Synapses Based on Lightly Oxidized Sulfide Films. , 2017, , . | | 0 |